



JST16A-800C 16A TRIAC

Rev.A.1.2

DESCRIPTION:

The JST16A-800C

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	3.5	kV
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ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit	
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	25	mA
				50	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	40	mA
				80	
I_H	$I_T=500mA$		MAX.	40	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	500	$V/\mu s$
$(dV/dt)_c$	$(dI/dt)_c=7A/ms$, $T_j=125$		MIN.	6	$V/\mu s$
t_{on}	$I_G=80mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter	Value(MAX.)	Unit	
V_{TM}	$I_{TM}=22.5A$ $t_p=380\mu s$ $T_j=25$	1.5	V	
V_{TO}	Threshold voltage $T_j=125$	0.77	V	
R_D	Dynamic resistance $T_j=125$	30	m	
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.5	mA


THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1	$/W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$/W$

RMS on-state current versus case
temperature

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